

ABSTRACT OF THE DISCLOSURE

In a gate electrode, above a first polycrystalline silicon film, a second polycrystalline silicon film, which has a predetermined silicon crystal face orientation directed with respect to and is smaller in crystal diameter than the first polycrystalline silicon film, is provided, so that even if there locally exist portions which are different in silicidization speed in forming a silicide layer in the second polycrystalline silicon film, the silicidization reaction with unreacted portions of the second polycrystalline silicon film can occur faster than the silicidization reaction with the first polycrystalline silicon film.